[ <del>-</del>	Hits	Search Text	DB	Time stamp
L Number	UICS			
1	102	((438/455).CCLS.) and (void or cavity or	USPAT;	2002/08/09
i _	0.1	recess) ((438/455).CCLS.) and (void or cavity)	US-PGPUB USPAT;	2002/08/09
2	81	((438/455).CCLS.) and (Void of Cavity)	US-PGPUB	12:06
3	21	(((438/455).CCLS.) and (void or cavity or	USPAT;	2002/08/09
	-	recess)) not (((438/455).CCLS.) and (void	US-PGPUB	12:44
		or cavity))		
4	10	(wafer same mirror) same (conductive adj	USPAT; US-PGPUB	2002/08/09
5	3349	layer)   optical adj cavit\$3	USPAT;	2002/08/09
	3349	optical adj cavitys	US-PGPUB	13:07
6	852	(optical adj cavit\$3) and electrode	USPAT;	2002/08/09
			US-PGPUB	12:52
8	167	(silicon and (silicon adj carbide) and	USPAT; US-PGPUB	2002/08/09
9	14	(gallium adj arsenide)) same wafer (silicon and (crystalline adj sapphire)	USPAT;	2002/08/09
9	14	and ceramic) same substrate	US-PGPUB	12:57
10	9	((silicon and (silicon adj carbide) and	USPAT;	2002/08/09
		(gallium adj arsenide)) same wafer) and	US-PGPUB	12:57
	F 3.0	mems ((optical adj cavit\$3) and electrode) and	USPAT;	2002/08/09
7	538	((optical adj cavit\$3) and electrode; and	US-PGPUB	13:05
13	1	(optical adj cavit\$3) and ((silicon and	USPAT;	2002/08/09
		(silicon adj carbide) and (gallium adj	US-PGPUB	13:11
		arsenide) and sapphire and ceramic) same		
1.6	4	(wafer or substrate)) (optical adj cavit\$3) and ((silicon and	USPAT;	2002/08/09
16	4	(silicon adj carbide) and (gallium adj	US-PGPUB	13:17
		arsenide)) same (wafer or substrate))		
17	603	recess near2 bevel\$2	USPAT;	2002/08/09
	4.7	t and the second of the second	US-PGPUB USPAT;	14:03 2002/08/09
18	41	mirror near2 (silicon adj (dioxide or oxide))	US-PGPUB	13:19
23	7	optical and mirror and ((recess or void	USPAT;	2002/08/09
		or cavity) near2 bevel\$2)	US-PGPUB	14:39
25	13	((438/455).CCLS.) and bevel\$2	USPAT;	2002/08/09
_	1572	mems	US-PGPUB USPAT	2002/07/28
1	1572	mems	001111	15:30
-	170	mems and bridge	USPAT	2002/07/28
	_			16:52
-	897	(bridge\$1 same (void or space or cavity or hole or recess)) and (438/\$.ccls. or	USPAT; US-PGPUB	2002/07/28
		257/\$.ccls.)	US-FGFUB	10.33
-	42	mems and bridge\$1 and (438/\$.ccls. or	USPAT;	2002/07/28
		257/\$.ccls.)	US-PGPUB	16:55
-	330	mems and bridge\$1	USPAT; US-PGPUB	2002/08/05
\	400	substrate near2 bond\$2 near2 wafer	USPAT;	2002/08/02
1 -	400	Substitute fieura bollaya fieura warer	US-PGPUB	14:29
-	1	(US-20020045297-\$).did.	US-PGPUB	2002/08/02
		13.3.3.5		13:22
-	824	(float\$3 or movable) and MEms	USPAT;	2002/08/02
_	667	((float\$3 or movable) and MEms) and	USPAT;	2002/08/02
	007	(bridge or member or element)	US-PGPUB	14:39
-	10	(((float\$3 or movable) and MEms) and	USPAT;	2002/08/07
		(bridge or member or element)) and	US-PGPUB	15:36
_	394	(substrate near2 bond\$3 near2 wafer) (mems or microelectronic) same movable	USPAT;	2002/08/05
-	394	(mems of microsiectionic) same movable	US-PGPUB	14:50
-	1	(US-20020086456-\$).did.	US-PGPUB	2002/08/05
	_		110777	14:18
-	7263	variable adj3 capacitor	USPAT; US-PGPUB	2002/08/05 14:51
_	187	accelerometer and mems	USPAT;	2002/08/05
	10/		US-PGPUB	14:51
-	5765	variable adj2 capacitor	USPAT;	2002/08/05
	<u> </u>		US-PGPUB	14:51

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-	5050	variable adj capacitor	USPAT;	2002/08/05
			US-PGPUB	14:51
-	76	(variable adj capacitor) and mems	USPAT;	2002/08/05
		•	US-PGPUB	14:52
l -	1	(US-6405592-\$).did.	USPAT	2002/08/05
				23:47
-	1	(US-6344417-\$).did.	USPAT	2002/08/05
				23:53
- 1	1	(US-6408878-\$).did.	USPAT	2002/08/06
				11:38
_	456	(438/455).CCLS.	USPAT;	2002/08/06
			US-PGPUB	13:29
-	1	(US-6356689-\$).did.	USPAT	2002/08/06
				14:29
_	1	(US-5656512-\$).did.	USPAT	2002/08/06
				16:06
_	259	(438/52).CCLS.	USPAT;	2002/08/07
[			US-PGPUB	14:04
_	275	(216/17).CCLS.	USPAT;	2002/08/07
			US-PGPUB	13:04
l –	9	((216/17).CCLS.) and (mems or	USPAT;	2002/08/07
		microelectric)	US-PGPUB	13:05
-	51	((438/52).CCLS.) and (mems or	USPAT;	2002/08/07
		microelectric)	US-PGPUB	13:12
_	251	(438/406).CCLS.	USPAT;	2002/08/07
			US-PGPUB	14:25
	35	((438/406).CCLS.) and (cavity or void)	USPAT;	2002/08/07
			US-PGPUB	14:11
ļ <u>-</u>	71	(438/379).CCLS.	USPAT;	2002/08/07
			US-PGPUB	14:25
-	128	(438/456).CCLS.	USPAT;	2002/08/07
			US-PGPUB	14:42
-	57	((438/456).CCLS.) and (cavity or void)	USPAT;	2002/08/07
			US-PGPUB	14:49
-	14	mems and accelerometer and bridge and	USPAT;	2002/08/07
		(void or cavity)	US-PGPUB	15:04
_	54	mems and bridge and (void or cavity) and	USPAT;	2002/08/07
	1	(substrate same wafer)	US-PGPUB	15:04
-	345	(moveable or movable) and mems and	USPAT;	2002/08/07
		(cavity or void)	US-PGPUB	15:45
-	8558	accelerometer	USPAT;	2002/08/07
		,	US-PGPUB	17:03
_	105	accelerometer and (cavity or void) and	USPAT;	2002/08/07
		(substrate near5 wafer)	US-PGPUB	15:54
_	1616	accelerometer\$1 and semiconductor\$1	USPAT;	2002/08/07
	1	·	US-PGPUB	17:04
_	194	(accelerometer\$1 and semiconductor\$1) and	USPAT;	2002/08/09
		(sacrificial\$1 adj layer\$1)	US-PGPUB	10:05
-	4	("4483194" "4922756" "5146435" "5013396").	PNSPAT	2002/08/09
				10:04
-	2	("3241374" "5719333").PN.	USPAT	2002/08/09
	1			10:04